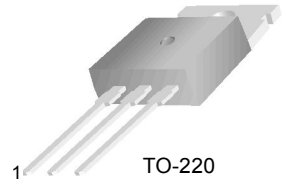
FAIRCHILD SEMICONDUCTOR®

October 2008

TIP100/TIP101/TIP102

NPN Epitaxial Silicon Darlington Transistor

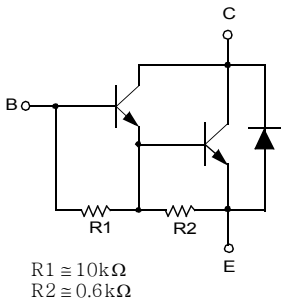
- Monolithic Construction With Built In Base-Emitter Shunt Resistors
- High DC Current Gain : h_{FE}=1000 @ V_{CE}=4V, I_C=3A (Min.)
- Collector-Emitter Sustaining Voltage
- Low Collector-Emitter Saturation Voltage
- Industrial Use
- Complementary to TIP105/106/107



TO-220

1.Base 2.Collector 3.Emitter

Equivalent Circuit



$R1 \cong 10k\Omega$
$R2 \cong 0.6k\Omega$

Absolute Maximum Ratings* T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage : TIP100	60	V
	: TIP101	80	V
	: TIP102	100	V
V_{CEO}	Collector-Emitter Voltage : TIP100	60	V
	: TIP101	80	V
	: TIP102	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current (DC)	8	A
I_{CP}	Collector Current (Pulse)	15	A
I_B	Base Current (DC)	1	A
P_C	Collector Dissipation (T_a=25°C)	2	W
	Collector Dissipation (T_C=25°C)	80	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	- 65 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V_{CEO}(sus)	Collector-Emitter Sustaining Voltage : TIP100 : TIP101 : TIP102	 I_C = 30mA, I_B = 0	 60 80 100			 V V V
I_{CEO}	Collector Cut-off Current : TIP100 : TIP101 : TIP102	 V_{CE} = 30V, I_B = 0 V_{CE} = 40V, I_B = 0 V_{CE} = 50V, I_B = 0			 50 50 50	 μA μA μA
I_{CBO}	Collector Cut-off Current : TIP100 : TIP101 : TIP102	 V_{CE} = 60V, I_E = 0 V_{CE} = 80V, I_E = 0 V_{CE} = 100V, I_E = 0			 50 50 50	 μA μA μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5V, I_C = 0			2	mA
h_{FE}	DC Current Gain	V_{CE} = 4V, I_C = 3A V_{CE} = 4V, I_C = 8A	1000 200		20000	
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 3A, I_B = 6mA I_C = 8A, I_B = 80mA			2 2.5	V V
V_{BE}(on)	Base-Emitter On Voltage	V_{CE} = 4V, I_C = 8A			2.8	V
C_{ob}	Output Capacitance	V_{CB} = 10V, I_E = 0, f = 0.1MHz			200	pF

* Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

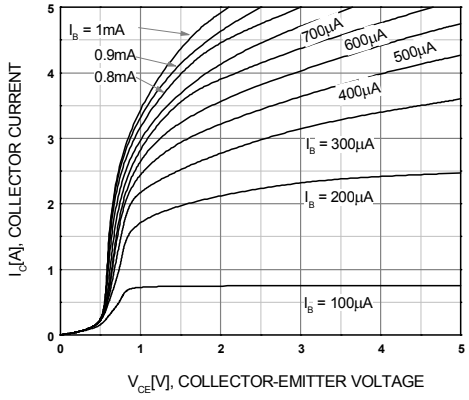


Figure 1. Static Characteristic

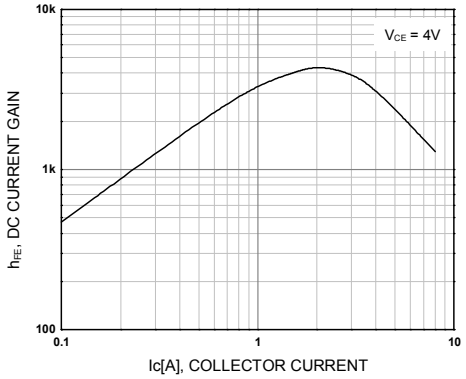


Figure 2. DC current Gain

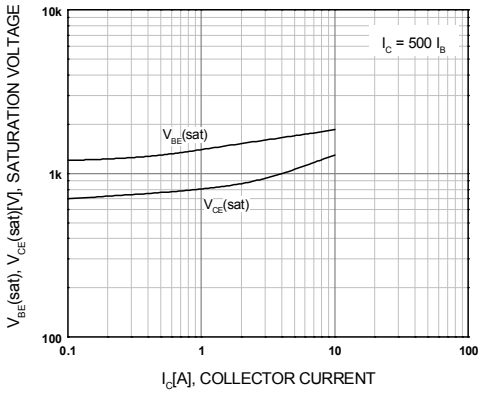


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

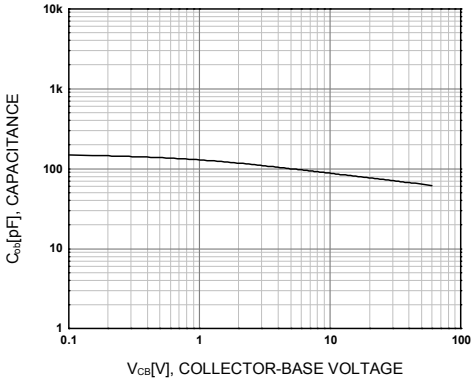


Figure 4. Collector Output Capacitance

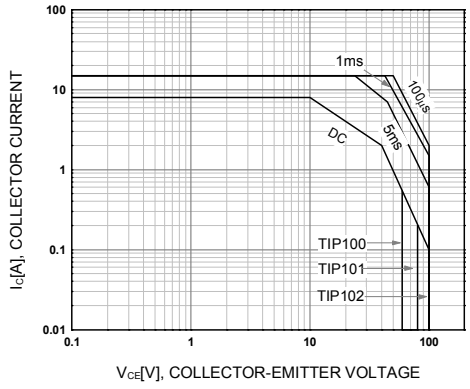


Figure 5. Safe Operating Area

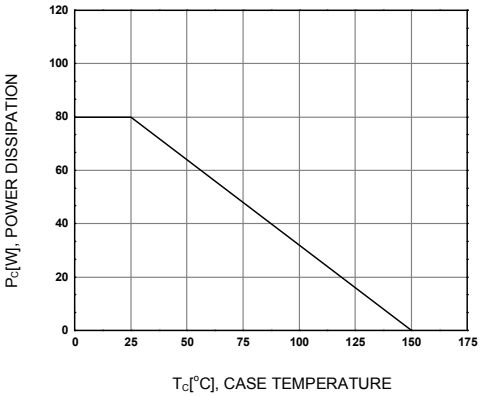
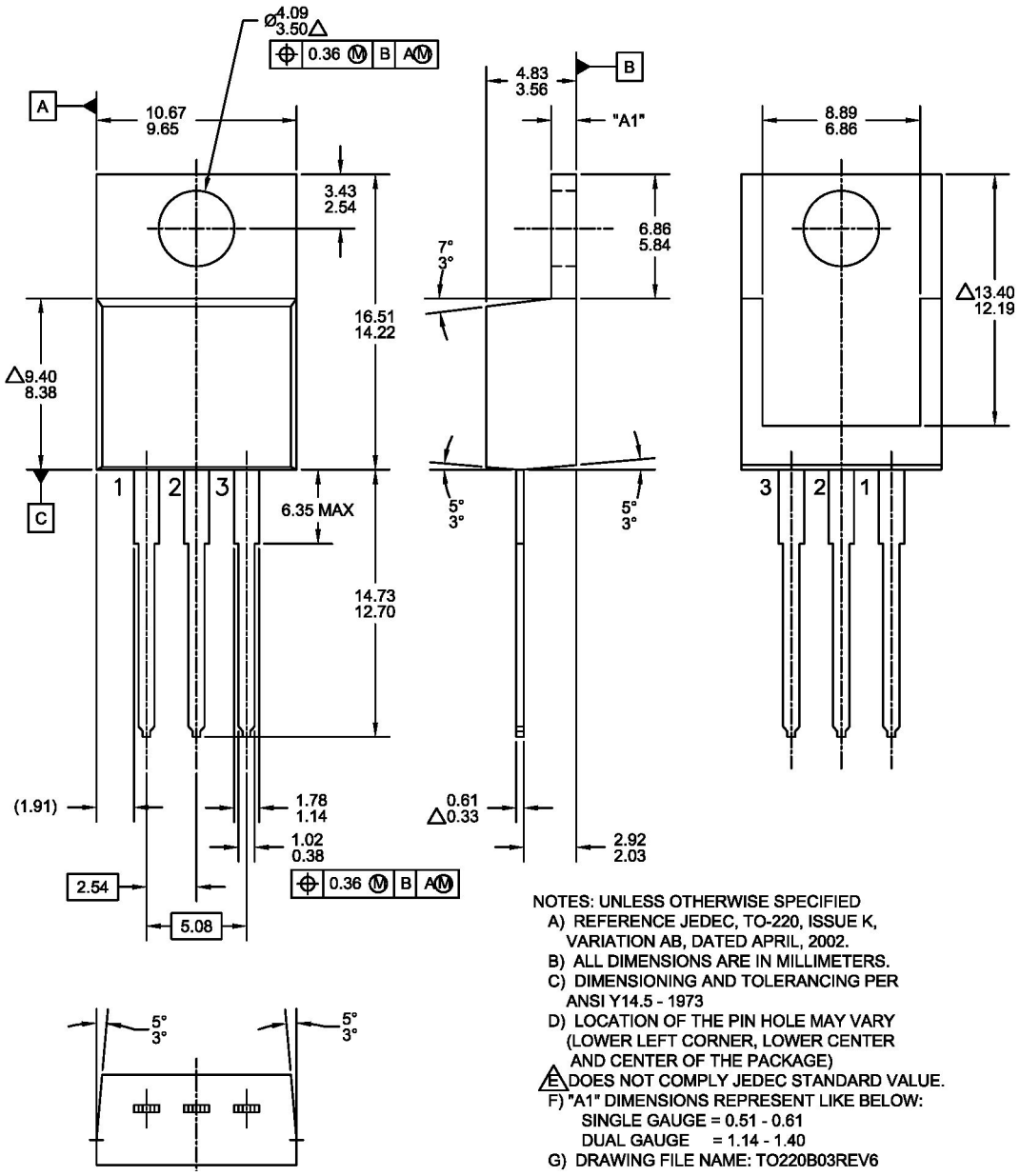


Figure 6. Power Derating

Mechanical Dimensions

TO220



NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
△E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS REPRESENT LIKE BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.14 - 1.40
G) DRAWING FILE NAME: TO220B03REV6

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